

Three-Phase IGBT BRIDGE, With Gate Driver and Optical Isolation

DESCRIPTION: A 600 VOLT, 150 AMP, THREE PHASE IGBT BRIDGE

ELECTRICAL CHARACTERISTICS PER IGBT DEVICE

($T_j=25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
IGBT SPECIFICATIONS					
Collector to Emitter Breakdown Voltage $I_C = 250 \mu\text{A}, V_{GE} = 0\text{V}$	BV_{CES}	600	-	-	V
Continuous Collector Current $T_C = 25^\circ\text{C}$ $T_C = 90^\circ\text{C}$	I_C	-	-	150 130	A
Pulsed Collector Current, 1mS	I_{CM}	-	-	250	A
Gate to Emitter Voltage	V_{GE}	-	-	+/-20	V
Gate-Emitter Leakage Current , $V_{GE} = +/-20\text{V}$	I_{GES}	-	-	+/- 100	nA
Zero Gate Voltage Collector Current $V_{CE} = 600 \text{ V}, V_{GE}=0\text{V} T_i=25^\circ\text{C}$ $V_{CE} = 480 \text{ V}, V_{GE}=0\text{V} T_i=125^\circ\text{C}$	I_{CES}	-	-	3 20	mA mA
Collector to Emitter Saturation Voltage, $T_C = 25^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$,	$V_{CE(SAT)}$	-	1.7	2.0	V
Maximum Thermal Resistance	$R_{\theta JC}$	-	-	0.25	$^\circ\text{C}/\text{W}$
Brake IGBT SPECIFICATIONS					
Continuous Collector Current $T_C = 25^\circ\text{C}$ $T_C = 90^\circ\text{C}$	I_C	-	-	80 60	A
Pulsed Collector Current, 0.5mS	I_{CM}	-	-	120	A
Maximum Thermal Resistance	$R_{\theta JC}$	-	-	0.45	$^\circ\text{C}/\text{W}$
Over-Temperature Shutdown					
Over-Temperature Shutdown	T_{sd}	100	110	120	$^\circ\text{C}$
Over-Temperature Shutdown Hysteresis			20		$^\circ\text{C}$
Over-Temperature Output	T_{co}		10		$10\text{mV}/^\circ\text{C}$

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PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
ULTRAFAST DIODES RATING AND CHARACTERISTICS					
Diode Peak Inverse Voltage	PIV	600	-	-	V
Continuous Forward Current, $T_C = 90^\circ\text{C}$	I_F	-	-	130	A
Forward Surge Current, $t_p = 10 \text{ msec}$	I_{FSM}	-	-	500	A
Diode Forward Voltage, $I_F = 100\text{A}$	V_F	-	1.4	1.7	V
Diode Reverse Recovery Time ($I_F=100\text{A}$, $V_{RR}=300\text{V}$, $di/dt=200 \text{ A}/\mu\text{s}$)	t_{rr}	-	90	160	nsec
Maximum Thermal Resistance	$R_{\theta JC}$	-	-	0.4	$^\circ\text{C}/\text{W}$
Gate Driver					
Supply Voltage	VCC	10	15	20	V
Input On Current	HIN, LIN	2		5.0	mA
Opto-Isolator Logic High Input Threshold	I_{th}	-	1.6	-	mA
Input Reverse Breakdown Voltage	BV_{in}	5.0	-	-	V
Input Forward Voltage @ $I_{in} = 5\text{mA}$	V_F	-	1.5	1.7	V
Under Voltage Lockout	VCCUV	7.0	-	9.7	V
ITRIP Reference Voltage ⁽¹⁾	Itrip-ref	1.45	1.5	1.55	V
Desaturation Over-Current Protection Blanking time ⁽²⁾	tbl	3	5	TBD	μsec
Input-to-Output Turn On Delay	t_{ond}	-		800	nsec
Output Turn On Rise Time	t_r	-		180	
Input-to-Output Turn Off Delay	t_{offd}	-		1000	
Output Turn Off Fall Time	t_f			160	
At $VCC=300\text{V}$, $IC=50\text{A}$, $T_C = 25$					
Input-Output Isolation Voltage	-	1000	-	-	V
Maximum operating Junction Temperature	T_{jmax}	-40	-	150	$^\circ\text{C}$
Maximum Storage Junction Temperature	T_{jmax}	-55	-	150	$^\circ\text{C}$

(1) ITRIP Cycle-by cycle current limit is internally set to 70A peak. The set point can be lowered by connecting a resistor between Itrip-ref and Gnd. The set point can be increased by connecting a resistor between Itrip-ref and +5V ref

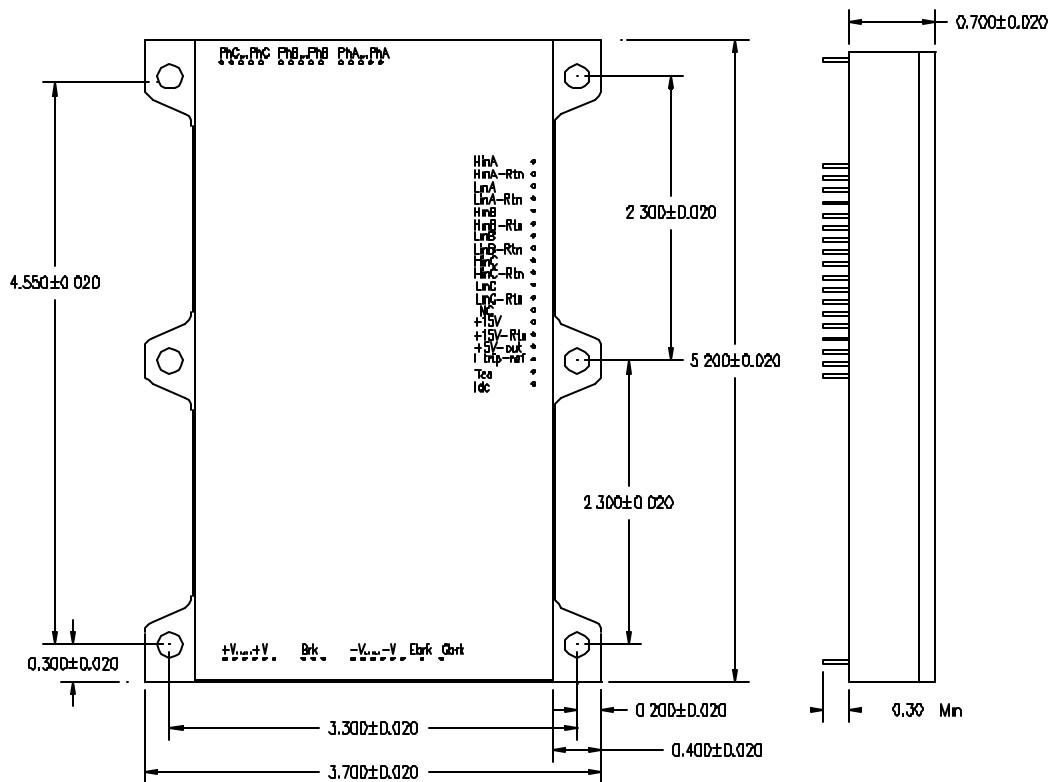
(2) Desaturation blanking maximum time is TBD and is only provided at the low-side IGBTs.

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Package Drawing:



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